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## PATENT APPLICATION

### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q66351

Toshiaki AOAI, et al.

Appln. No.: 09/961,281

Group Art Unit: 1752

Confirmation No.: 6134

Examiner: Rosemary E. Ashton

Filed: September 25, 2001

For: POSITIVE RESIST COMPOSITION

#### **COMMENTS ON EXAMINER'S STATEMENT OF REASONS FOR ALLOWANCE IN NOTICE OF ALLOWANCE AND STATEMENT OF SUBSTANCE OF INTERVIEW**

#### **MAIL STOP ISSUE FEE**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In the Statement of Reasons for Allowance in the Notice of Allowance, the Examiner states that "surfactants are well known in the art and one of ordinary skill would know how to use them in a resist composition," citing Aoai et al., U.S. Patent No. 5,693,452, Lin et al., U.S. Patent No. 6,087,064, Elsaesser et al., U.S. Patent No. 6,100,004, and Kodama et al., U.S. Patent No. 6,265,135.

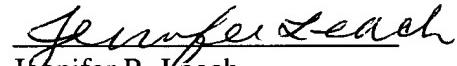
Applicants submit that the present invention is directed to a specific polymer containing a fluorine atom and a specific surfactant containing at least one of a silicon atom and a fluorine atom. By this, the present invention can obtain a specific effect as disclosed in the specification. Even if each cited reference describes a surfactant, each cited reference does not disclose the

Appln. No.: 09/961,281  
Comments on Examiner's Statement of Reasons  
For Allowance in Notice of Allowance and  
Statement of Substance of Interview

resist composition comprising the specific polymer and the specific surfactant in the present invention at all.

With respect to the Interview Summary mailed October 29, 2004, Applicants' representative and the Examiner determined that the abstract filed with the application on September 25, 2001 is proper.

Respectfully submitted,

  
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CUSTOMER NUMBER

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